



SOT-89-3L Plastic-Encapsulate Transistors

PXT8550 TRANSISTOR (PNP)

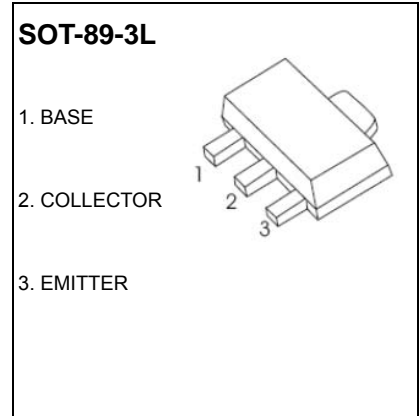
FEATURES

Compliment to PXT8050

MARKING: Y2

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-40	V
V _{CE0}	Collector-Emitter Voltage	-25	V
V _{EB0}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-1.5	A
P _C	Collector Power Dissipation	0.5	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C



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ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E =0	-40		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -0.1mA, I _B =0	-25		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} = -40 V, I _E =0		-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} = -20V, I _B =0		-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0		-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} = -1V, I _C = -100mA	85	400	
	h _{FE(2)}	V _{CE} = -1V, I _C = -800mA	40		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-800mA, I _B = -80mA		-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-800mA, I _B = -80mA		-1.2	V
Base-emitter on voltage	V _{BE(on)}	I _C =-1V, V _{CE} =-10mA		-1	V
Base-emitter positive favor voltage	V _{BEF}	I _B =-1A		-1.55	V
Transition frequency	f _T	V _{CE} = -10V, I _C = -50mA	100		MHZ
output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		20	pF

CLASSIFICATION OF h_{FE(1)}

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400